

STEALTH™ Diode

50 A, 600 V

FFH50US60S-F085

Description

The FFH50US60S-F085 is a STEALTH™ diode optimized for low loss performance in output rectification. The STEALTH family exhibits low reverse recovery current (I_{RR}), low V_F and soft recovery under typical operating conditions. It has a low forward-voltage drop and is of silicon nitride passivated.

This device is intended for use as a freewheel/clamping diode in various automotive switching power supplies and other power switching applications. Its low stored charge as well as Stealth and soft recovery characteristics minimize ringing and electrical noise while reduce the overall power loss.

Features

- Stealth Recovery, $t_{rr} = 163$ ns (Typ.) @ $I_F = 50$ A)
- Low Forward Voltage ($V_F = 1.69$ V (Max.) @ $I_F = 50$ A)
- Avalanche Energy Rated
- AEC-Q101 Qualified
- This Device is Pb-Free

Applications

- Automotive DCDC Converter
- Automotive On Board Charger
- Switching Power Supply
- Power Switching Circuits

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

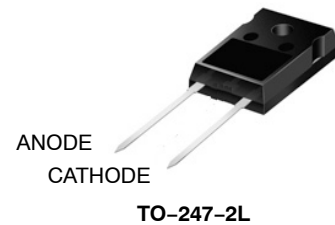
Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	600	V
Working Peak Reverse Voltage	V_{RWM}	600	V
DC Blocking Voltage	V_R	600	V
Average Rectified Forward Current ($T_C = 25^\circ\text{C}$)	$I_{F(AV)}$	50	A
Non-repetitive Peak Surge Current (Halfwave 1 Phase 50 Hz)	I_{FSM}	150	A
Avalanche Energy (1 A, 40 mH)	E_{AVL}	20	mJ
Operating Junction and Storage Temperature	T_J, T_{STG}	-55 to +175	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

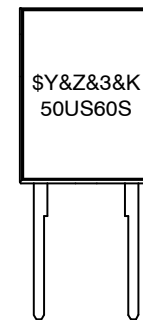


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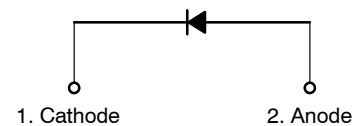
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MARKING DIAGRAM



\$Y = ON Semiconductor Logo
 &Z = Assembly Plant Code
 &3 = Numeric Date Code
 &K = Lot Code
 50US60S = Specific Device Code



ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FFH50US60S-F085

PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Package	Tube	Quantity
FFH50US60S	FFH50US60S-F085	TO247-2L	-	30

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit		
I_R	Instantaneous Reverse Current	$V_R = 600\text{ V}$	$T_C = 25^\circ\text{C}$	-	-	100	μA	
			$T_C = 175^\circ\text{C}$	-	-	1000	μA	
V_{FM} (Note 1)	Instantaneous Forward Voltage	$I_F = 50\text{ A}$	$T_C = 25^\circ\text{C}$	-	1.27	1.69	V	
			$T_C = 175^\circ\text{C}$	-	1.19	1.57	V	
t_{rr} (Note 2)	Reverse Recovery Time	$I_F = 1\text{ A}$, $di/dt = 200\text{ A}/\mu\text{s}$, $V_R = 390\text{ V}$	$T_C = 25^\circ\text{C}$	-	41	82	ns	
			$T_C = 25^\circ\text{C}$	$I_F = 50\text{ A}$, $di/dt = 200\text{ A}/\mu\text{s}$, $V_R = 390\text{ V}$	-	163	-	ns
				$T_C = 175^\circ\text{C}$	-	364	-	ns
t_a t_b Q_{rr}	Reverse Recovery Time Reverse Recovery Charge	$I_F = 50\text{ A}$, $di/dt = 200\text{ A}/\mu\text{s}$, $V_R = 390\text{ V}$	$T_C = 25^\circ\text{C}$	-	65 98 886	- - -	ns ns nC	

1. Pulse : Test Pulse width = 300 μs , Duty Cycle = 2%

2. Guaranteed by design

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TEST CIRCUITS AND WAVEFORMS

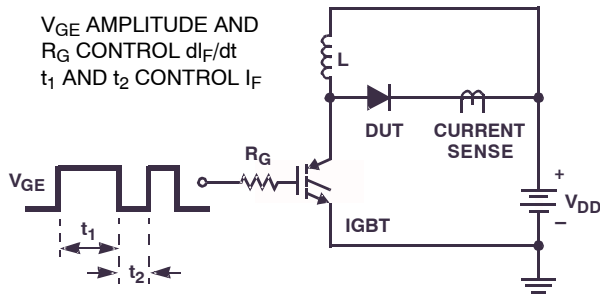


Figure 1. T_{rr} Test Circuit

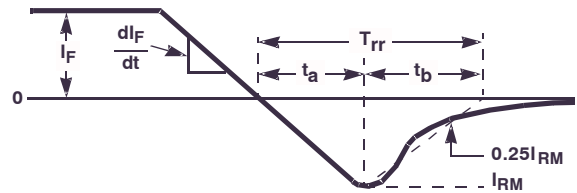


Figure 2. T_{rr} Waveforms and Definitions

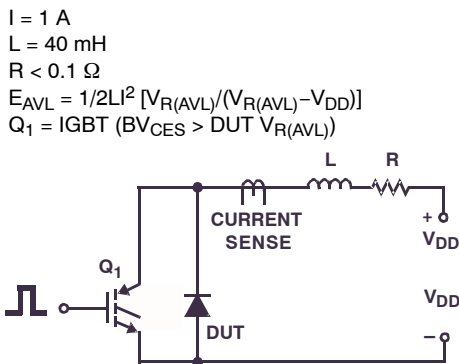


Figure 3. Avalanche Energy Test Circuit

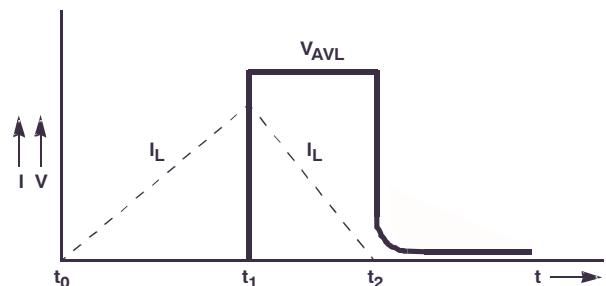


Figure 4. Avalanche Current and Voltage Waveforms

TYPICAL PERFORMANCE CHARACTERISTICS

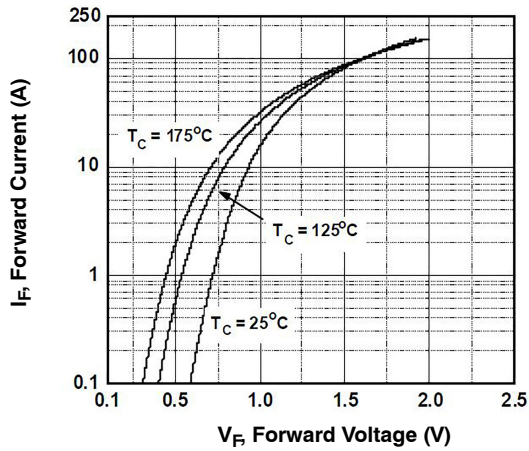


Figure 5. Typical Forward Voltage Drop vs. Forward Current

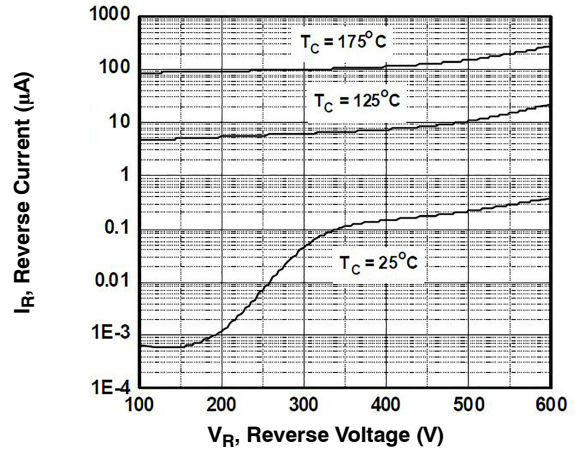


Figure 6. Typical Reverse Current vs. Reverse Voltage

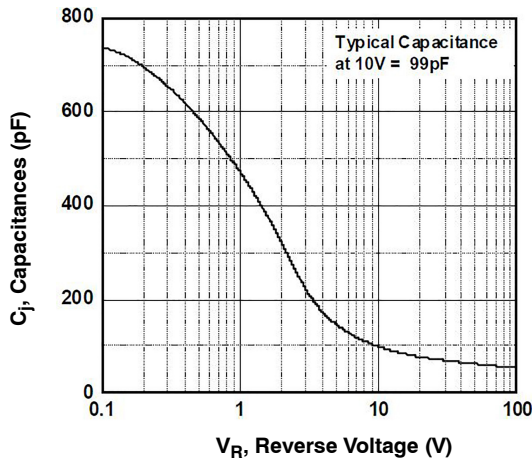


Figure 7. Typical Junction Capacitance

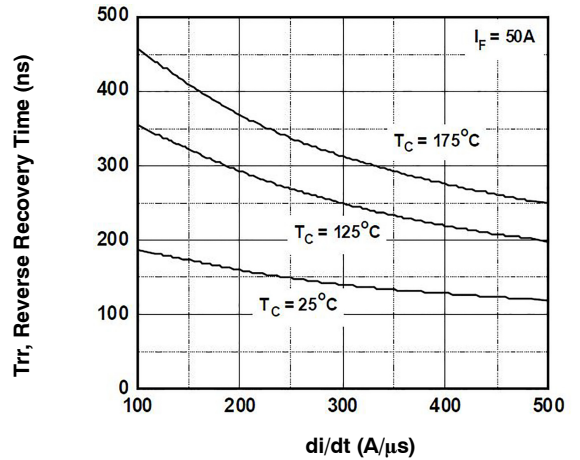


Figure 8. Typical Reverse Recovery Time vs. di/dt

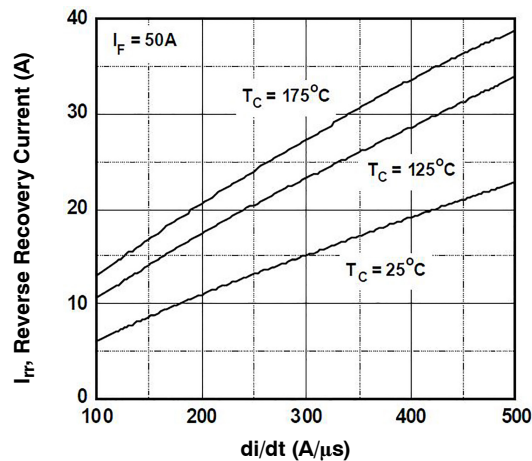


Figure 9. Typical Reverse Recovery Current vs. di/dt

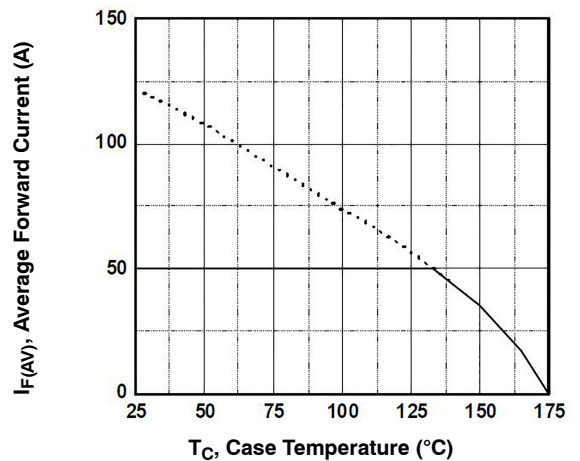


Figure 10. Forward Current Derating Curve

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

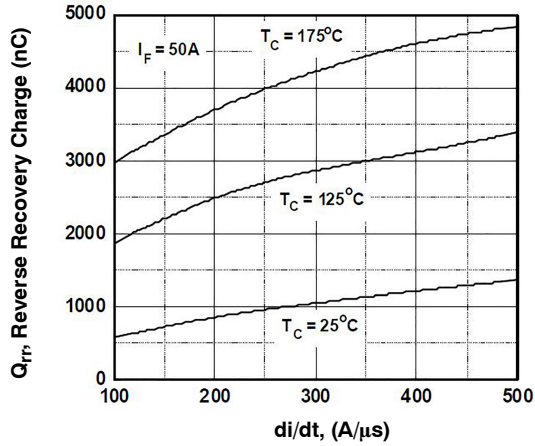


Figure 11. Reverse Recovery Charge

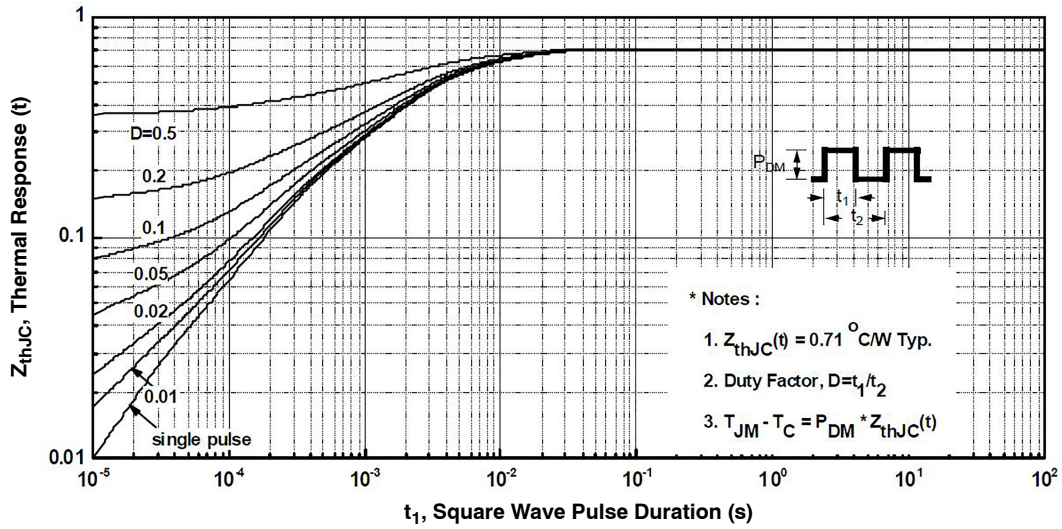


Figure 12. Transient Thermal Response Curve

MECHANICAL CASE OUTLINE

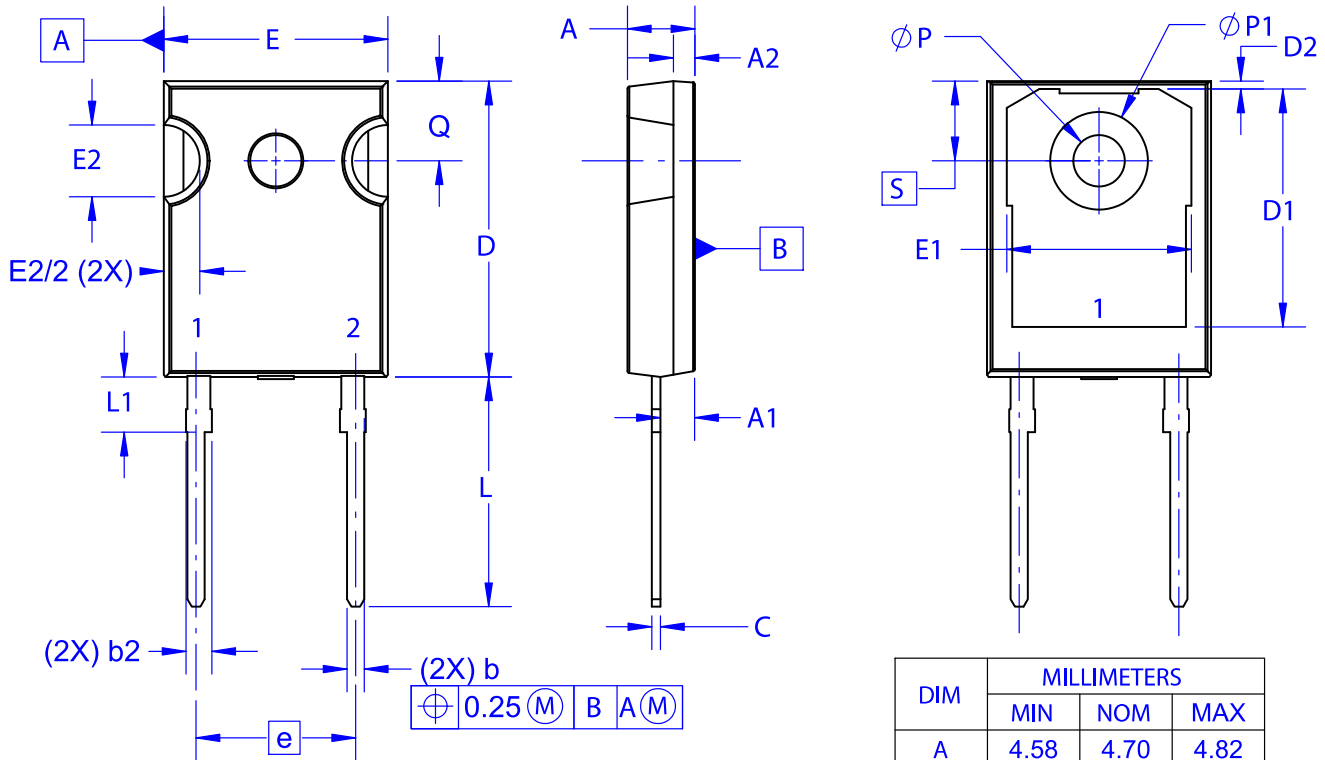
PACKAGE DIMENSIONS

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TO-247-2LD
CASE 340CL
ISSUE A

DATE 03 DEC 2019

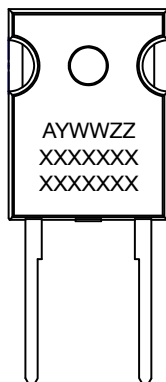


⊕ 0.25 (M) B A (M)

NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
- D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.29	2.40	2.66
A2	1.30	1.50	1.70
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
c	0.51	0.61	0.71
D	20.32	20.57	20.82
D1	16.37	16.57	16.77
D2	0.51	0.93	1.35
E	15.37	15.62	15.87
E1	12.81	~	~
E2	4.96	5.08	5.20
e	~	11.12	~
L	15.75	16.00	16.25
L1	3.69	3.81	3.93
∅P	3.51	3.58	3.65
∅P1	6.61	6.73	6.85
Q	5.34	5.46	5.58
S	5.34	5.46	5.58

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